CY62138F MoBL®

2-Mbit (256K x 8) Static RAM

Features

- High speed: 45 ns
- Wide voltage range: 4.5 V – 5.5 V
- Pin compatible with CY62138V
- Ultra low standby power
  - Typical standby current: 1 µA
  - Maximum standby current: 5 µA
- Ultra low active power
  - Typical active current: 1.6 mA @ f = 1 MHz
- Easy memory expansion with $\overline{CE}_1$, CE_2, and $\overline{OE}$ features
- Automatic power down when deselected
- complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 32-pin SOIC and 32-pin thin small outline package (TSOP) II packages

Functional Description [1]

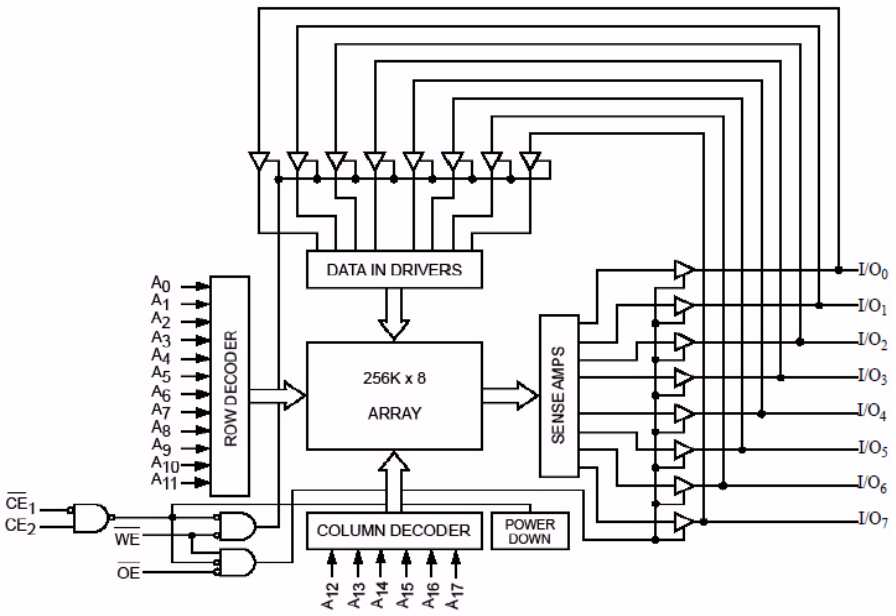
The CY62138F is a high performance CMOS static RAM organized as 256K words by 8 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{CE}_1$ HIGH or CE_2 LOW).

To write to the device, take Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and Write Enable ($\overline{WE}$) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{17}).

To read from the device, take Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and output enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the I/O pins.

The eight input and output pins (I/O_0 through I/O_7) are placed in a high impedance state when the device is deselected ($\overline{CE}_1$ HIGH or CE_2 LOW), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}_1$ LOW and CE_2 HIGH and $\overline{WE}$ LOW).

Logic Block Diagram



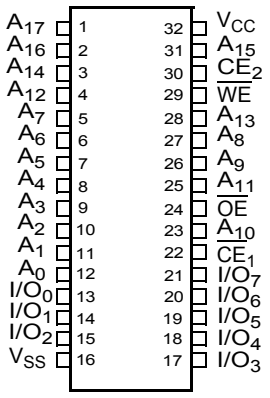
Note
1. For best practice recommendations, refer to the Cypress application note *"System Design Guidelines"* at http://www.cypress.com.

Contents

Pin Configuration

32-Pin SOIC/TSOP II Pinout

Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1MHz		f = f_{max}			
	Min	Typ [2]	Max		Typ [2]	Max	Typ [2]	Max	Typ [2]	Max
CY62138FLL	4.5 V	5.0 V	5.5 V	45	1.6	2.5	13	18	1	5

Notes

2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, T_A = 25 °C.

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ..... –65 °C to + 150 °C

Ambient temperature with power applied ..... –55 °C to + 125 °C

Supply voltage to ground potential ..... –0.5 V to 6.0 V (V_{CCmax} + 0.5 V)

DC voltage applied to outputs in High-Z state [3, 4] ..... –0.5 V to 6.0 V (V_{CCmax} + 0.5 V)

DC Input Voltage [3, 4] ..... –0.5 V to 6.0 V (V_{CCmax} + 0.5 V)

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001 V (MIL–STD–883, Method 3015)

Latch-up Current ..... > 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC} [5]
CY62138FLL	Industrial	–40 °C to +85 °C	4.5 V to 5.5 V

Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		45 ns			Unit
				Min	Typ [6]	Max	
V_{OH}	Output HIGH voltage	I_{OH} = –1.0 mA		2.4	–	–	V
V_{OL}	Output LOW voltage	I_{OL} = 2.1 mA		–	–	0.4	V
V_{IH}	Input HIGH voltage	V_{CC} = 4.5 V to 5.5 V		2.2	–	V_{CC} + 0.5	V
V_{IL}	Input LOW voltage	V_{CC} = 4.5 V to 5.5 V		–0.5	–	0.8	V
I_{IX}	Input leakage current	GND ≤ V_I ≤ V_{CC}		–1	–	+1	µA
I_{OZ}	Outputcleakage Current	GND ≤ V_O ≤ V_{CC}, Output disabled		–1	–	+1	µA
I_{CC}	V_{CC} operating supply Current	f = f_{max} = 1/t_{RC}	V_{CC} = $V_{CC(max)}$, I_{OUT} = 0 mA CMOS levels	–	13	18	mA
		f = 1 MHz		–	1.6	2.5	
I_{SB2} [7]	Automatic CE Power-down current CMOS inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2 V or CE_2 ≤ 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V, f = 0, V_{CC} = $V_{CC(max)}$		–	1	5	µA

Capacitance

Parameter[8]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

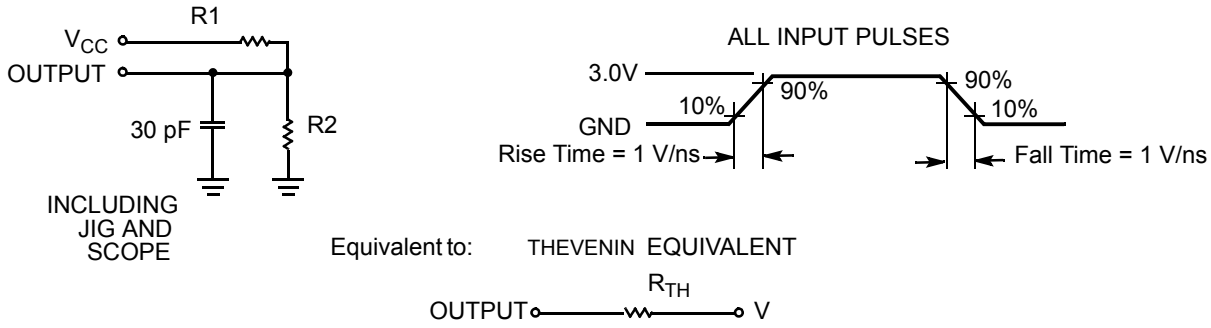
Thermal Resistance

Parameter[8]	Description	Test Conditions	SOIC	TSOP II	Unit
Θ_{JA}	Thermal resistance (Junction to Ambient)	Still air, soldered on a 3 × 4.5 inch two-layer printed circuit board	44.53	44.16	°C / W
Θ_{JC}	Thermal resistance (Junction to Case)		24.05	11.97	°C / W

Notes

3. $V_{IL(min)}$ = –2.0 V for pulse durations less than 20 ns.
4. $V_{IH(max)}$ = V_{CC}+0.75 V for pulse durations less than 20 ns.
5. Full device AC operation assumes a 100 µs ramp time from 0 to V_{CC}(min) and 200 µs wait time after V_{CC} stabilization.
6. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ)}$, T_A = 25 °C
7. Chip enables ($\overline{CE}_1$ and CE_2) must be at CMOS level to meet the I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
8. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms

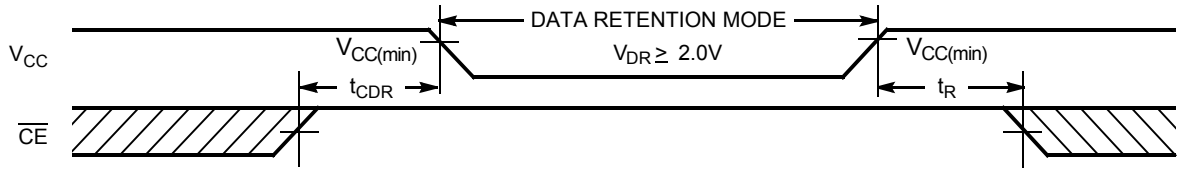


Parameters	5.0 V	Unit
R1	1800	Ω
R2	990	Ω
R_{TH}	639	Ω
V_{TH}	1.77	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min	Typ [9]	Max	Unit
V_{DR}	V_{CC} for Data retention		2.0	–	–	V
I_{CCDR} [10]	Data retention current	V_{CC}= V_{DR}, $\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC}$ - 0.2V or $V_{IN} \leq 0.2V$	–	1	5	µA
t_{CDR} [9]	Chip deselect to data retention time		0	–	–	ns
t_R [11]	Operation recovery time		45	–	–	ns

Data Retention Waveform [12]



Notes:

9. Tested initially and after any design or process changes that may affect these parameters.Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25$ °C
10. Chip enables ($\overline{CE}_1$ and CE_2) must be at CMOS level to meet the I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
11. Full device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.
12. $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.

Switching Characteristics (Over the Operating Range)

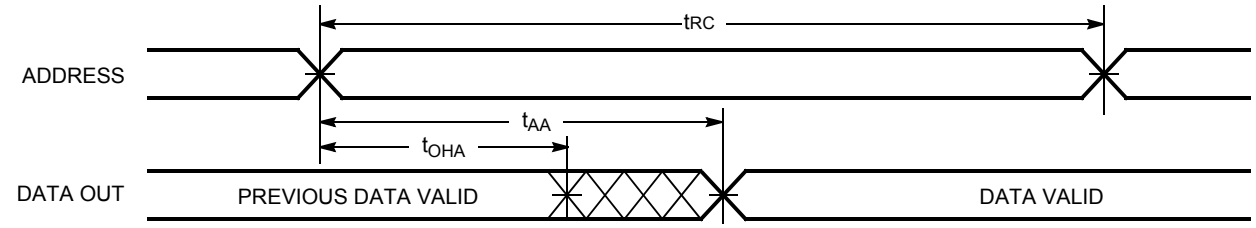
Parameter[13]	Description	45 ns		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}_1$ LOW and $\overline{CE}_2$ HIGH to data valid	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z [14]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z [14, 15]	–	18	ns
t_{LZCE}	$\overline{CE}_1$ LOW and $\overline{CE}_2$ HIGH to Low Z [14]	10	–	ns
t_{HZCE}	$\overline{CE}_1$ HIGH or $\overline{CE}_2$ LOW to High-Z [14, 15]	–	18	ns
t_{PU}	$\overline{CE}_1$ LOW and $\overline{CE}_2$ HIGH to power-up	0	–	ns
t_{PD}	$\overline{CE}_1$ HIGH or $\overline{CE}_2$ LOW to power-down	–	45	ns
Write Cycle [16]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}_1$ LOW and $\overline{CE}_2$ HIGH to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{SD}	Data setup to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z [14, 15]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z [14]	10	–	ns

Notes

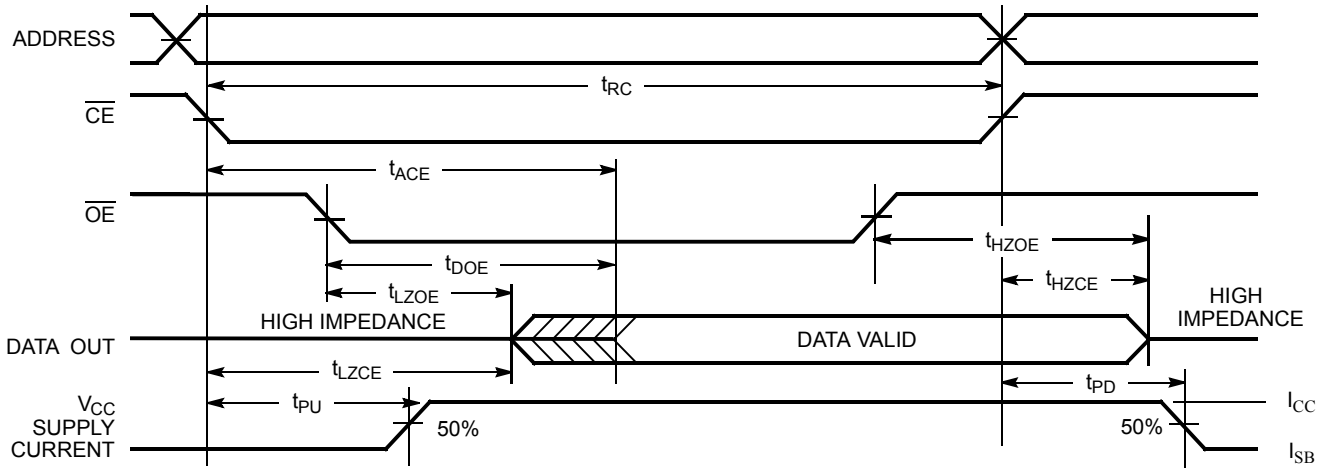
13. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns (1V/ns) or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the AC Test Loads and Waveforms on page 5.
14. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
15. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
16. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}_1$ = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.

Switching Waveforms

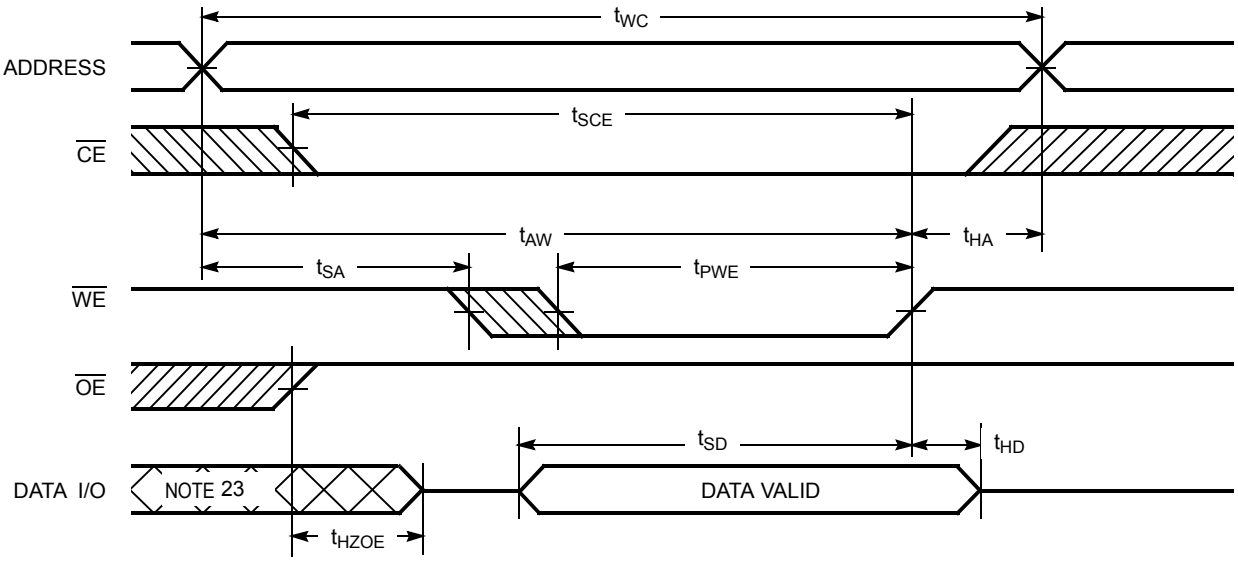
Read Cycle 1 (Address transition controlled) [17, 18]



Read Cycle No. 2 ($\overline{OE}$ controlled) [18, 19, 22]



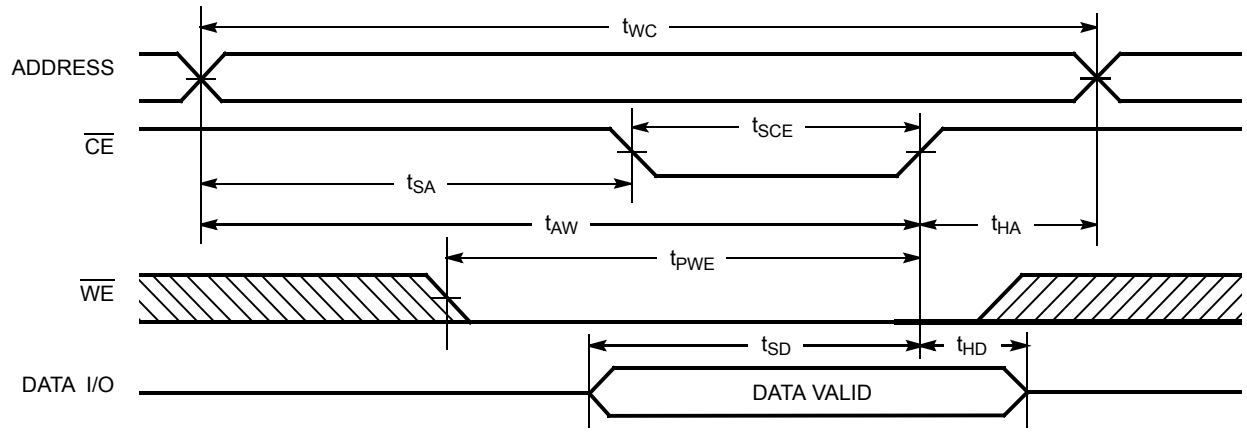
Write Cycle No. 1 ($\overline{WE}$ controlled) [16, 20, 21, 22]



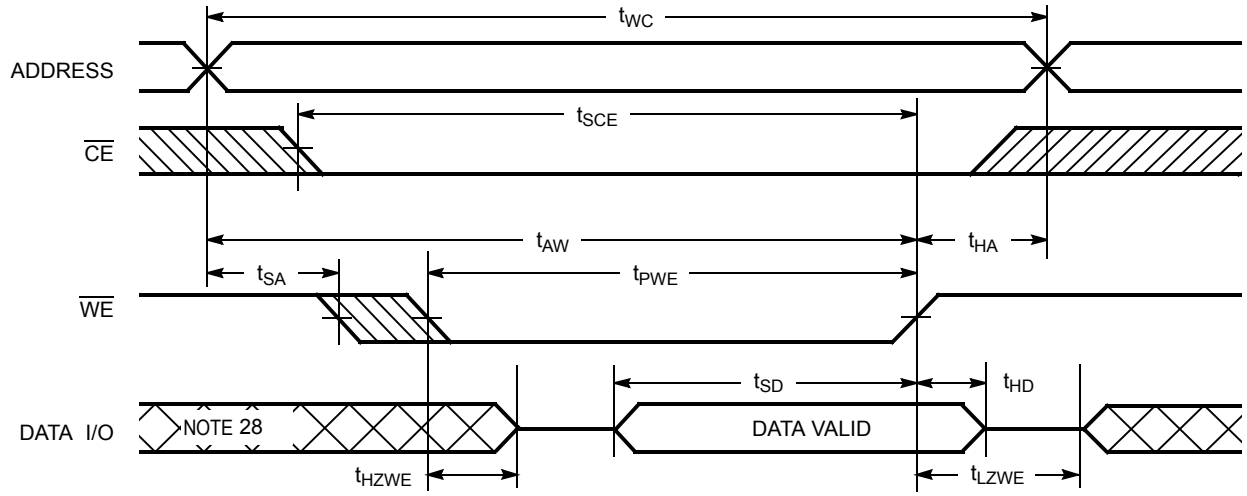
Notes:
17. The device is continuously selected. $\overline{OE}$, $\overline{CE}_1$ = V_{IL}, CE_2 = V_{IH}.
18. $\overline{WE}$ is HIGH for read cycle.
19. Address valid before or similar to $\overline{CE}_1$ transition LOW and CE_2 transition HIGH.
20. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
21. If $\overline{CE}_1$ goes HIGH or CE_2 goes LOW simultaneously with $\overline{WE}$ HIGH, the output remains in high impedance state.
22. $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH
23. During this period, the I/Os are in output state. Do not apply input signals

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE1}$ or $\overline{CE2}$ controlled) [24, 25, 26, 27]



Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) [24, 27]



Notes
24. $\overline{CE}$ is the logical combination of $\overline{CE_1}$ and $\overline{CE_2}$. When $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE_1}$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH
25. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE_1}$ = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write
26. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
27. If $\overline{CE_1}$ goes HIGH or $\overline{CE_2}$ goes LOW simultaneously with $\overline{WE}$ HIGH, the output remains in high impedance state.
28. During this period, the I/Os are in output state. Do not apply input signals.

Truth Table

$\overline{CE_1}$	$\overline{CE_2}$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X[29]	X	X	High Z	Deselect / Power-down	Standby (I_{SB})
X[29]	L	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	Data out	Read	Active (I_{CC})
L	H	H	H	High-Z	Output disabled	Active (I_{CC})
L	H	L	X	Data in	Write	Active (I_{CC})

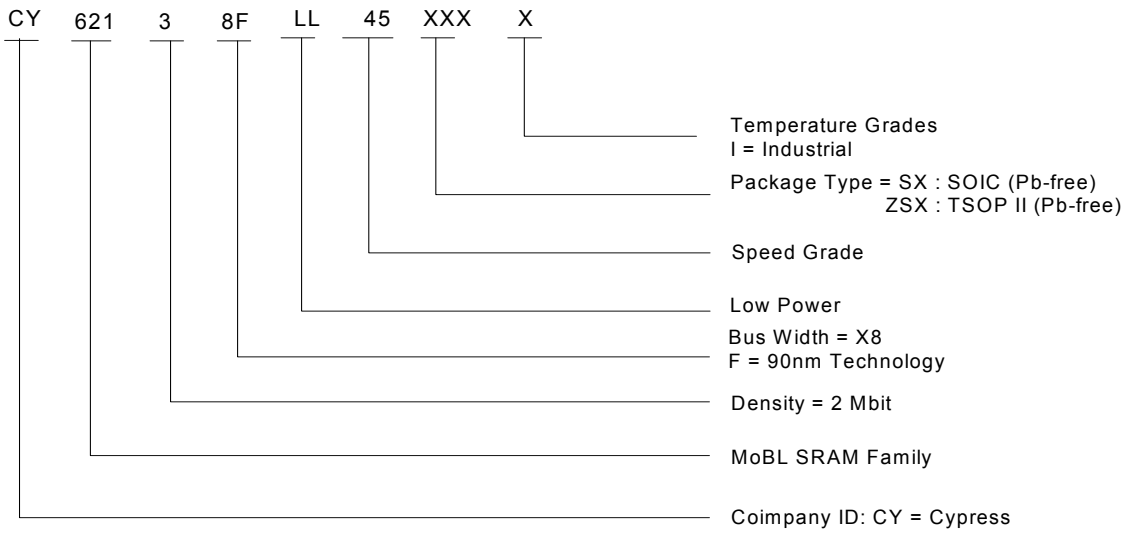
Note
29. The 'X' (Don't care) state for the Chip enables ($\overline{CE}_1$ and $\overline{CE}_2$) in the truth table refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62138FLL-45SXI	51-85081	32-pin Small Outline Integrated Circuit (Pb-free)	Industrial
	CY62138FLL-45ZSXI	51-85095	32-pin Thin Small Outline Package II (Pb-free)	

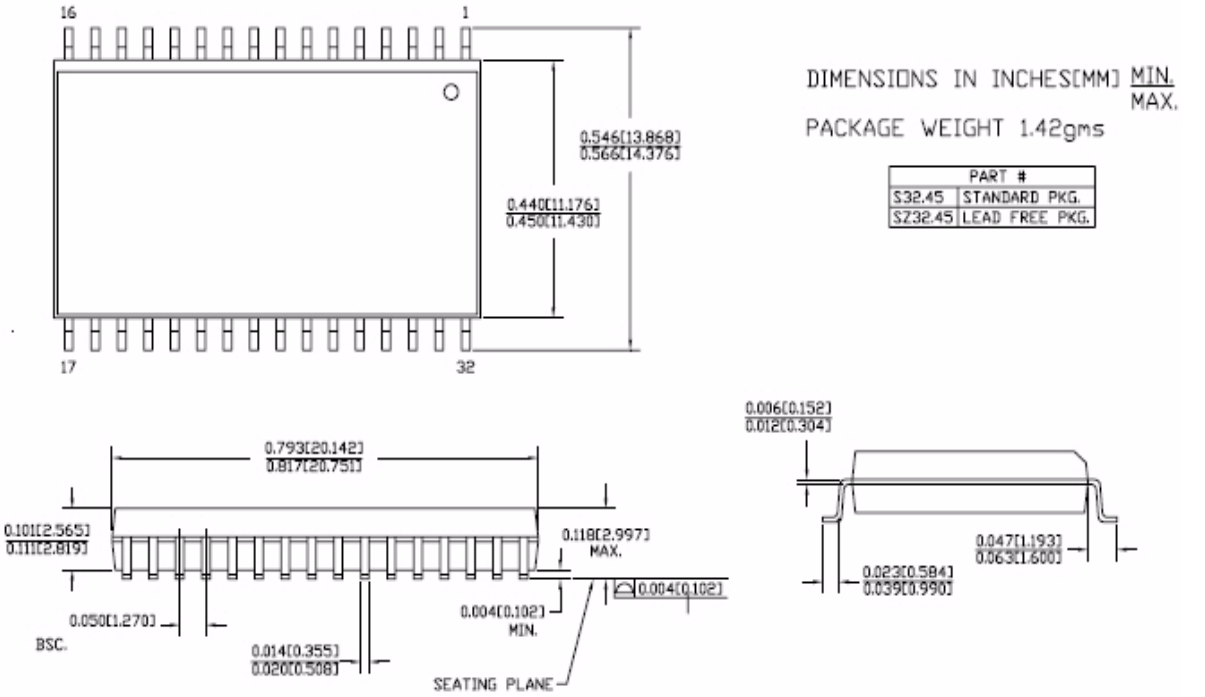
Contact your local Cypress sales representative for availability of these parts.

Ordering Code Definition



Package Diagrams

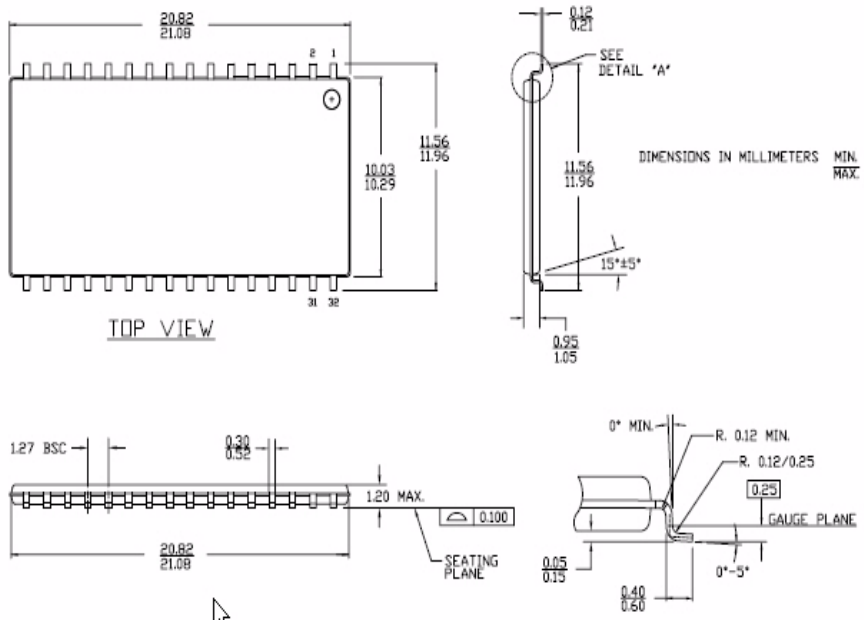
Figure 1. 32-pin (450 Mil) Molded SOIC, 51-85081



51-85081-*C

Package Diagrams (continued)

Figure 2. 32-Pin TSOP II, 51-85095



51-85095-*A

Acronyms

Acronym	Description
CMOS	complementary metal oxide semiconductor
I/O	input/output
SRAM	static random access memory
VFBGA	very fine ball grid array
TSOP	thin small outline package
SOIC	small outline integrated circuit

Documents Conventions

Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
µA	microamperes
mA	milliampere
MHz	megahertz
ns	nanoseconds
pF	picofarads
V	volts
Ω	ohms
W	watts

Document History Page

Document Title: CY62138F MoBL® 2-Mbit (256K x 8) Static RAM Document Number: 001-13194				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	797956	See ECN	VKN	New Data Sheet
*A	940341	See ECN	VKN	Added footnote #7 related to I_{SB2} and I_{CCDR}
*B	3055174	13/10/2010	RAME	Updated As per new template Added Acronyms and Units of Measure table. Added Ordering Code Definition. Footnotes updated Updated Package Diagram Figure 1 and Figure 2.
*C	3061313	15/10/2010	RAME	Minor change: Corrected “IO” to “I/O”

Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at Cypress Locations.

Products

Automotive	cypress.com/go/automotive
Clocks & Buffers	cypress.com/go/clocks
Interface	cypress.com/go/interface
Lighting & Power Control	cypress.com/go/powerpsoc cypress.com/go/plc
Memory	cypress.com/go/memory
Optical & Image Sensing	cypress.com/go/image
PSoC	cypress.com/go/psoc
Touch Sensing	cypress.com/go/touch
USB Controllers	cypress.com/go/USB
Wireless/RF	cypress.com/go/wireless

PSoC Solutions

psoc.cypress.com/solutions

PSoC 1 | PSoC 3 | PSoC 5